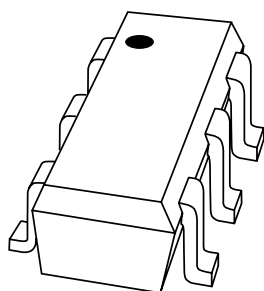


DATA SHEET



PUMD6 NPN/PNP resistor-equipped transistor

Product specification
Supersedes data of 1997 Dec 15

1999 May 28

NPN/PNP resistor-equipped transistor

PUMD6

FEATURES

- Transistors with different polarity, each with a built-in bias resistor R1 (typ. 4.7 kΩ)
- No mutual interference between the transistors
- Simplification of circuit design
- Reduces number of components and board space.

APPLICATIONS

- Especially suitable for space reduction in interface and driver circuits
- Inverter circuit configurations without use of external resistors.

DESCRIPTION

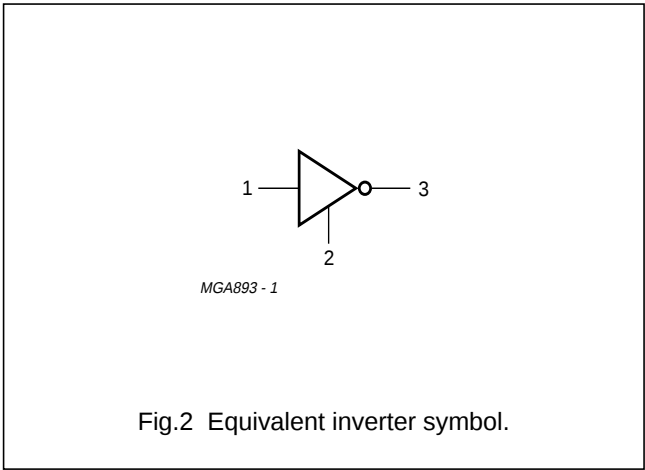
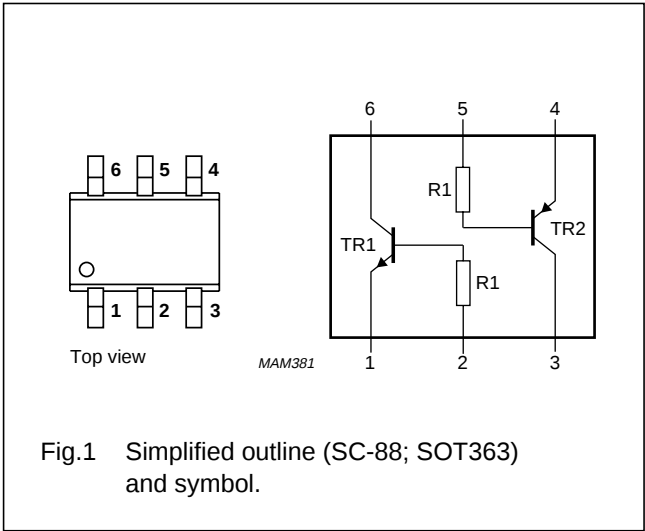
NPN/PNP resistor-equipped transistors in an SC-88 (SOT363) plastic package.

PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2

MARKING

TYPE NUMBER	MARKING CODE
PUMD6	Dt6



NPN/PNP resistor-equipped transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
V_{CBO}	collector-base voltage	open emitter	–	50	V
V_{CEO}	collector-emitter voltage	open base	–	50	V
V_{EBO}	emitter-base voltage	open collector	–	10	V
V_i	input voltage				
	positive		–	+40	V
	negative		–	–10	V
I_o	output current (DC)		–	100	mA
I_{CM}	peak collector current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN/PNP resistor-equipped transistor

PUMD6

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	416	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

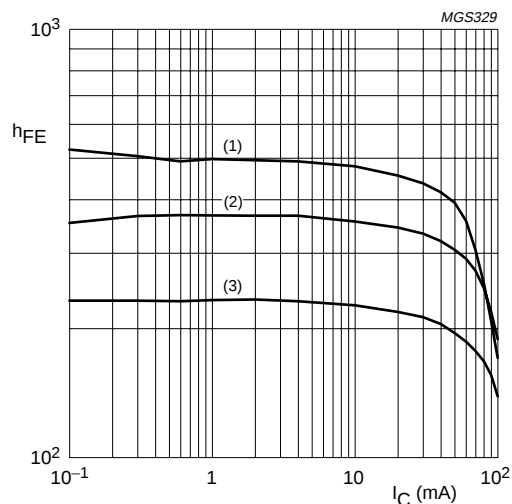
CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity						
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 50\text{ V}$	–	–	100	nA
I_{CEO}	collector cut-off current	$I_B = 0; V_{CE} = 30\text{ V}$	–	–	1	μA
		$I_B = 0; V_{CE} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	50	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	200	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 5\text{ mA}; I_B = 0.25\text{ mA}$	–	–	100	mV
R1	input resistor		3.3	4.7	6.1	k Ω
NPN transistor						
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	2.5	pF
PNP transistor						
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	–	3	pF

NPN/PNP resistor-equipped transistor

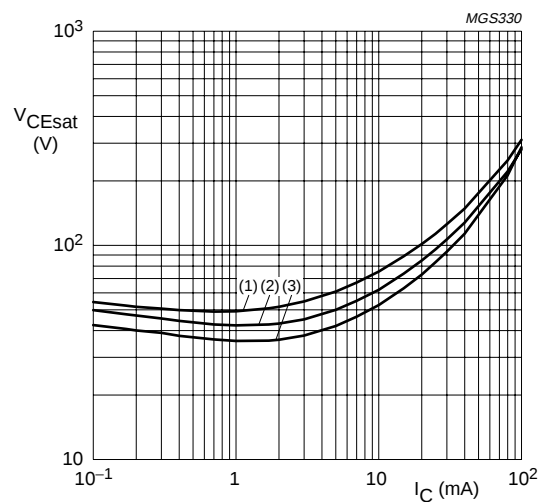
PUMD6



TR1 (NPN); $V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

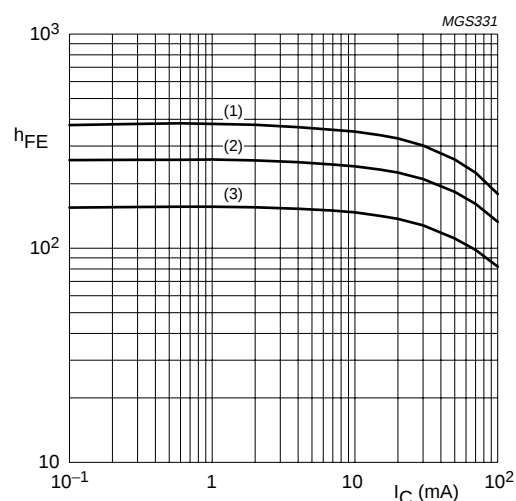
Fig.3 DC current gain as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

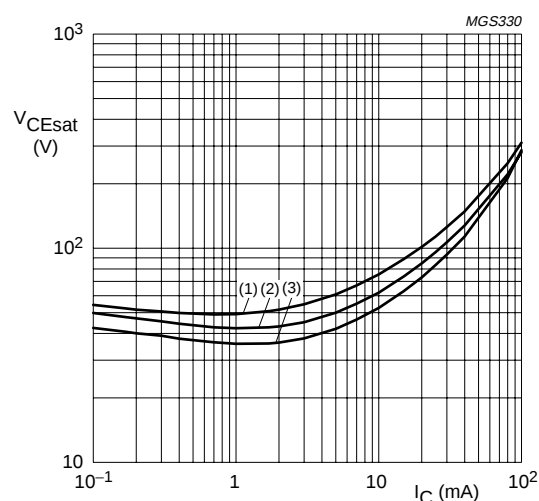
Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -5 \text{ V}$.

- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

Fig.5 DC current gain as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.

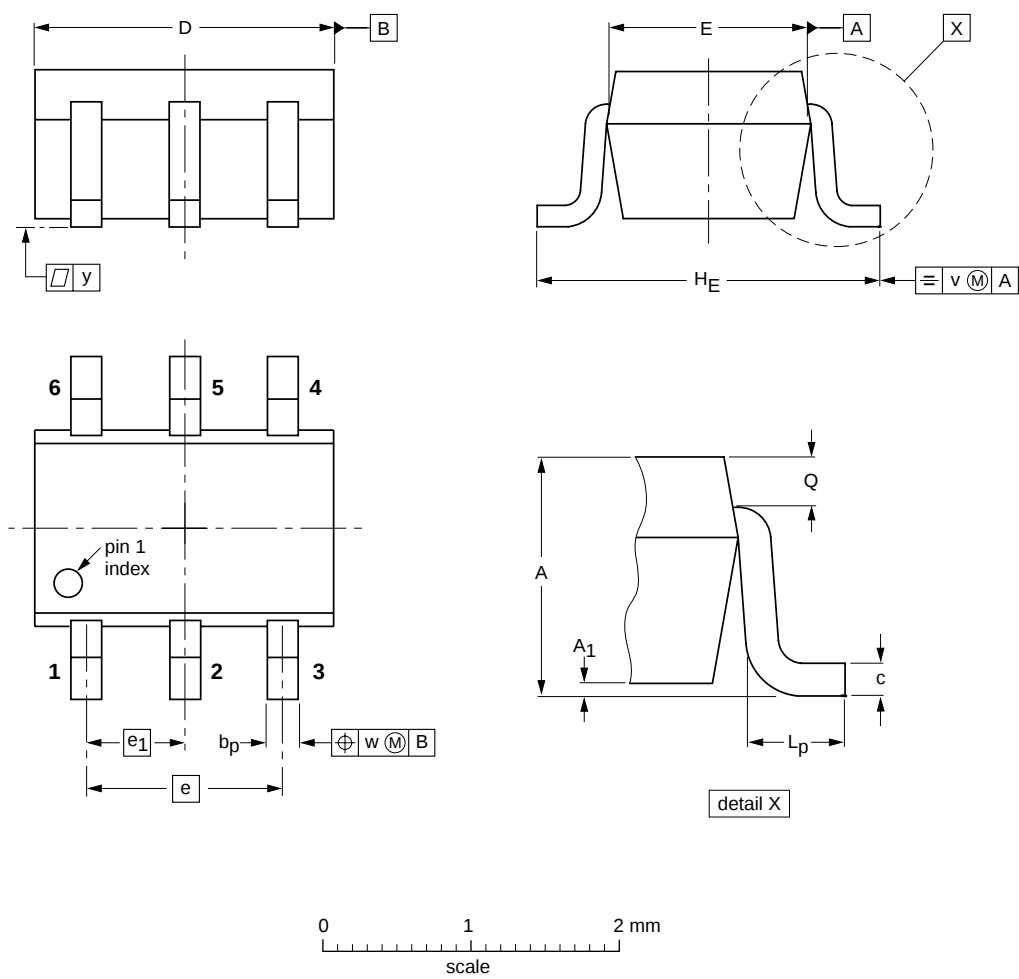
NPN/PNP resistor-equipped transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	HE	Lp	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT363			SC-88			97-02-28

NPN/PNP resistor-equipped transistor

PUMD6

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Printed in The Netherlands

115002/02/pp8

Date of release: 1999 May 28

Document order number: 9397 750 05342

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